

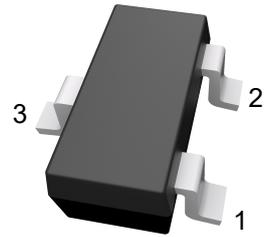
### Features

- $V_{DS} = -30V$   $I_D = -4.5A$
- $R_{DS(ON)} = 60m\Omega(max)$  @-10V
- Halogen and Antimony Free

### Applications

- Load Switch and in PWM Applications

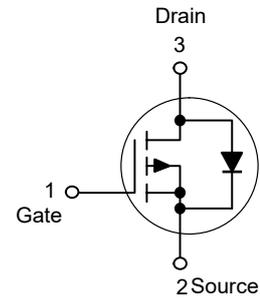
SOT-23-3



1. Gate 2. Source 3. Drain

Marking: P1

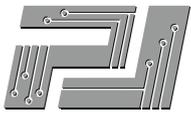
### Schematic Diagram



### Absolute Maximum Ratings

Ratings at  $T_A = 25^\circ C$  unless otherwise specified.

Parameter	Symbol	Value	Units
Drain-Source Voltage	$-V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 12$	V
Continuous Drain Current	$-I_D$	4.5	A
Power Dissipation	$P_D$	1.4	W
Junction and Storage Temperature Range	$T_J, T_{STG}$	150, -55 to 150	$^\circ C$
<b>Thermal Characteristics</b>			
Parameter	Symbol	Typ.	Units
Maximum Junction-to-Ambient <sup>Note1</sup>	$R_{\theta JA}$	89	$^\circ C/W$

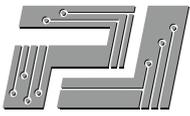


**Electrical Characteristics** ( $T_C=25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
<b>Static Characteristics</b>						
Drain-source breakdown voltage	$-V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250\mu A$	30	--	--	V
Drain to Source Leakage Current	$-I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$	--	--	1	$\mu A$
Gate-body leakage current	$I_{GSS}$	$V_{GS} = \pm 12V, V_{DS} = 0V$	--	--	$\pm 100$	nA
Gate threshold voltage <sup>Note2</sup>	$-V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	0.7	1	1.3	V
Drain-source on-resistance <sup>Note2</sup>	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -4.1A$	--	--	60	m $\Omega$
		$V_{GS} = -4.5V, I_D = -4A$	--	--	70	m $\Omega$
		$V_{GS} = -2.5V, I_D = -1A$	--	--	90	m $\Omega$
Forward transconductance <sup>Note2</sup>	$g_{FS}$	$V_{DS} = -5V, I_D = -5A$	7	--	--	S
<b>Dynamic characteristics</b>						
Input Capacitance	$C_{iss}$	$V_{DS} = -15V, V_{GS} = 0V, f = 1MHz$	--	880	--	pF
Output Capacitance	$C_{oss}$		--	105	--	
Reverse Transfer Capacitance	$C_{rss}$		--	65	--	
<b>Switching Characteristics</b>						
Turn-on delay time	$t_{d(on)}$	$V_{DS} = -15V,$ $V_{GS} = -10V, R_{GEN}$ $= 6\Omega, I_D = -4.2A$	--	7	--	ns
Turn-on rise time	$t_r$		--	3	--	
Turn-off delay time	$t_{d(off)}$		--	30	--	
Turn-off fall time	$t_f$		--	12	--	
Total gate charge	$Q_g$	$V_{DD} = -15V, V_{GS} = -4.5V, I_D = -4.2A$	--	8.5	--	nC
Gate-source charge	$Q_{gs}$		--	1.8	--	
Gate-drain charge	$Q_{gd}$		--	2.7	--	
<b>Source-Drain Diode characteristics</b>						
Diode Forward voltage	$-V_{DS}$	$V_{GS} = 0V, I_S = -4.2A$	--	--	1.2	V

Notes:

1. Surface mounted on FR4 board,  $t \leq 10$  sec.
2. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .



### Typical Characteristic Curves

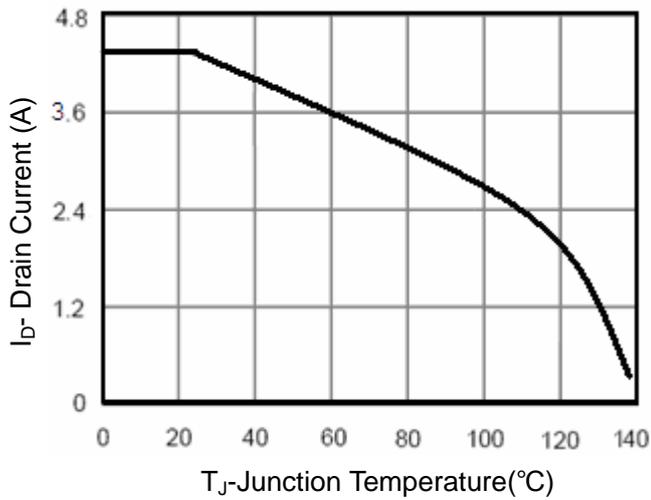


Figure 1 Drain Current

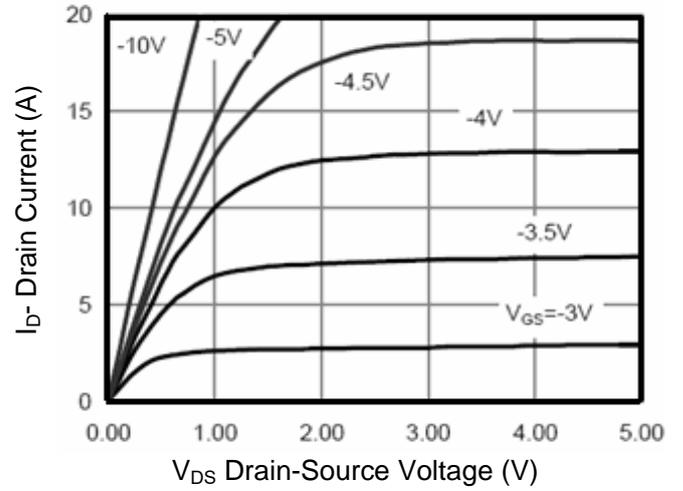


Figure 2 Output Characteristics

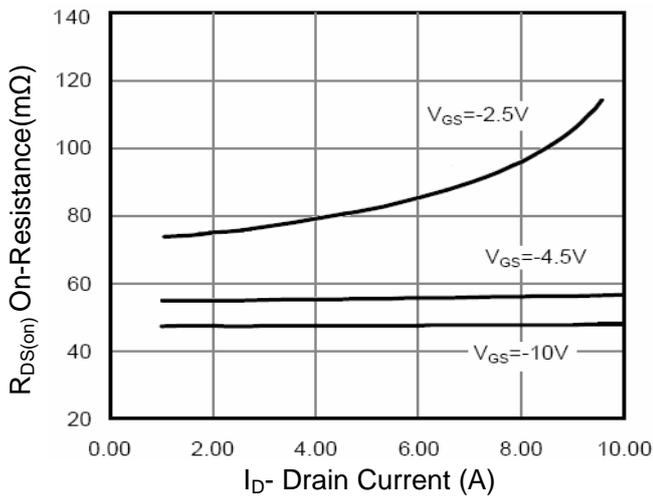


Figure 3 Drain-Source On-Resistance

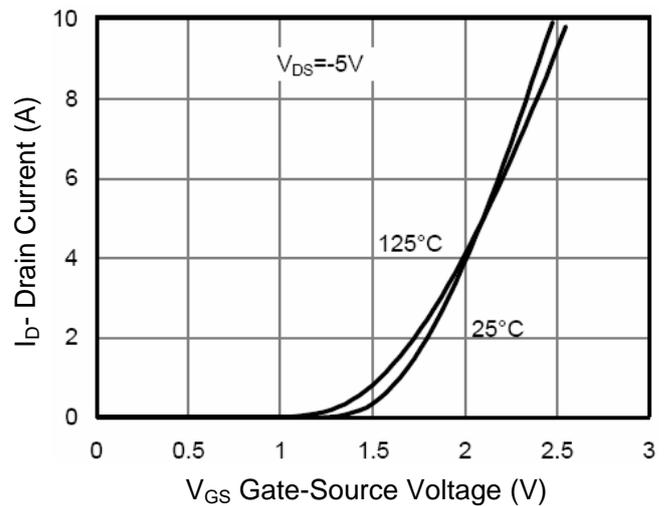


Figure 4 Transfer Characteristics

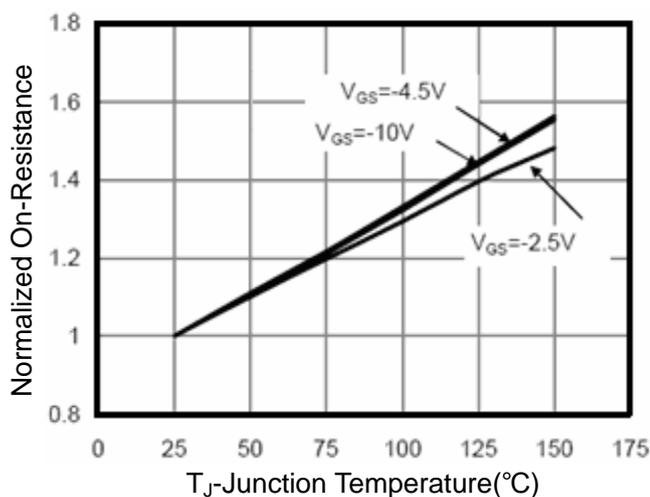


Figure 5 Drain-Source On-Resistance

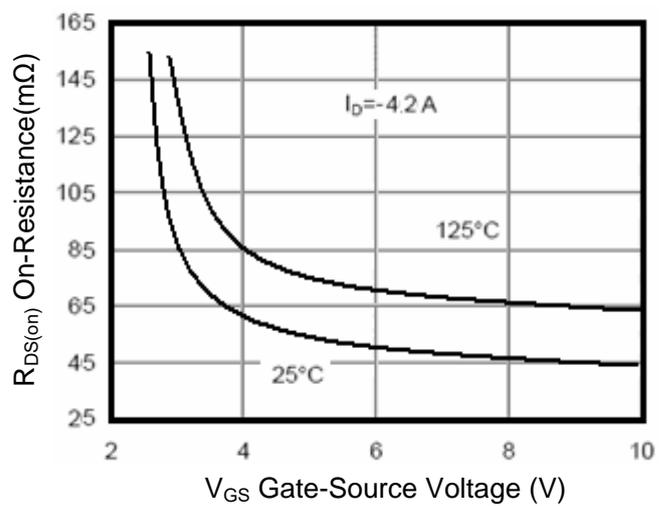


Figure 6  $R_{DS(on)}$  vs  $V_{GS}$

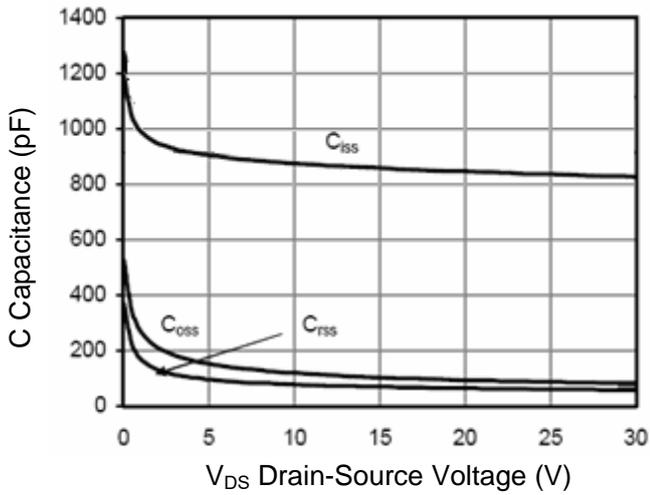


Figure 7 Capacitance vs V<sub>DS</sub>

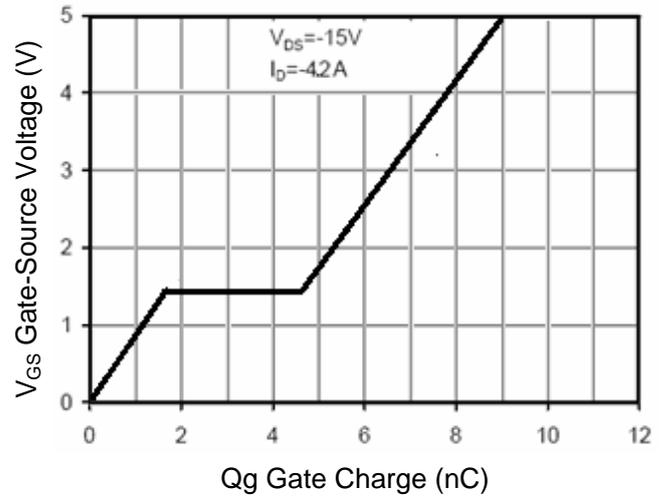


Figure 8 Gate Charge

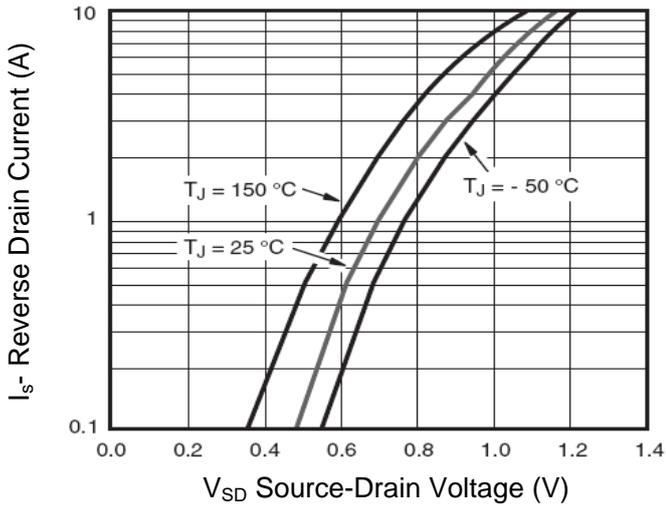


Figure 9 Source- Drain Diode Forward

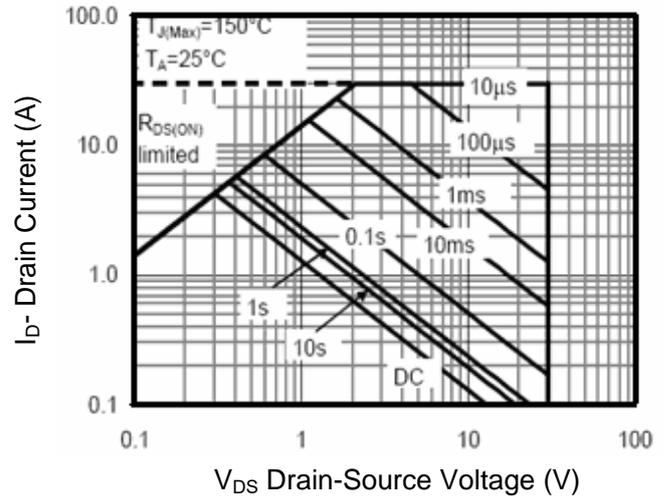


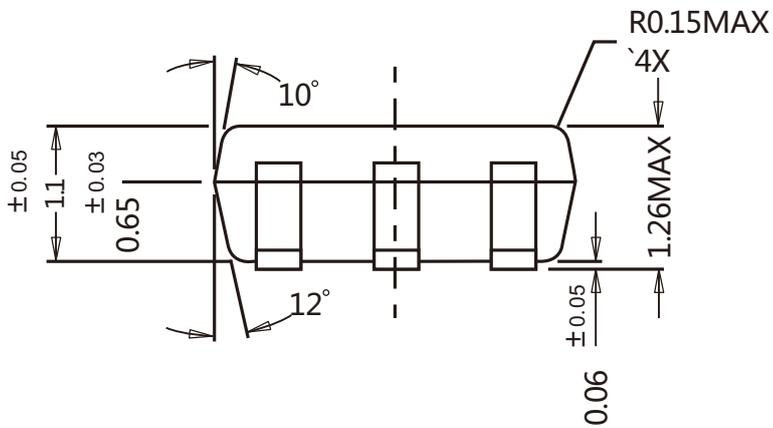
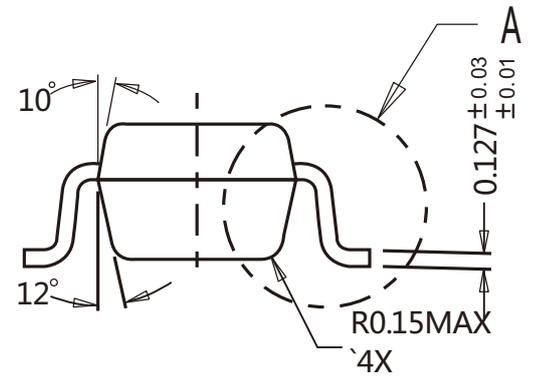
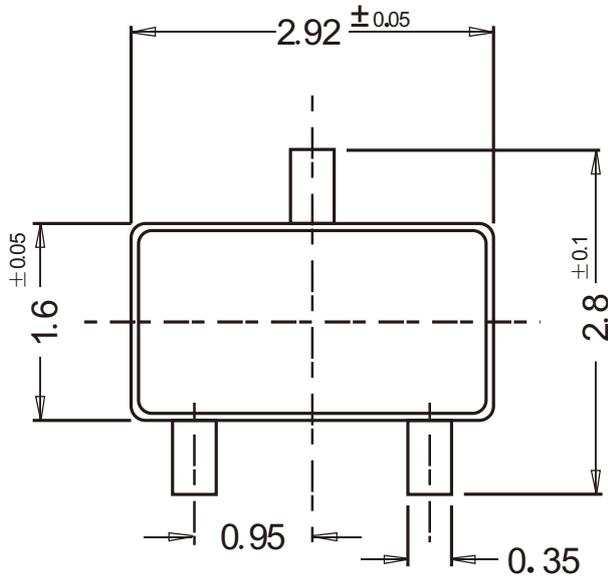
Figure 10 Safe Operation Area



### Package Outline

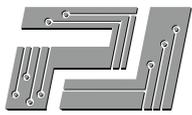
SOT-23-3

Dimensions in mm



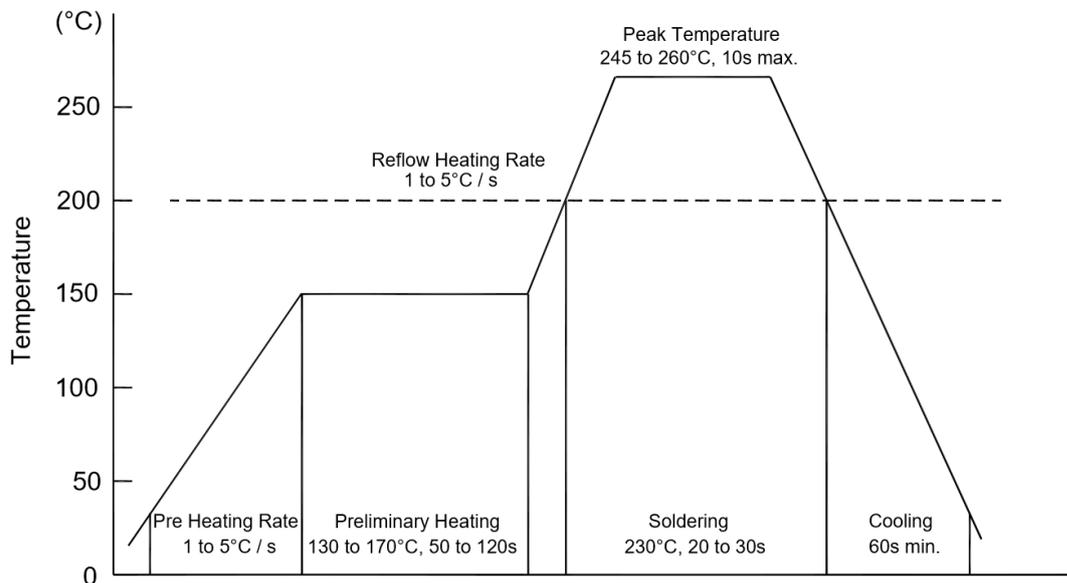
### Ordering Information

Device	Package	Shipping
PJM3401PSC	SOT-23-3	3000PCS/Reel&Tape



## Conditions of Soldering And Storage

### ◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

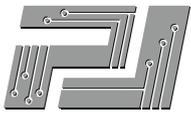
- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

### ◆ Conditions of hand soldering

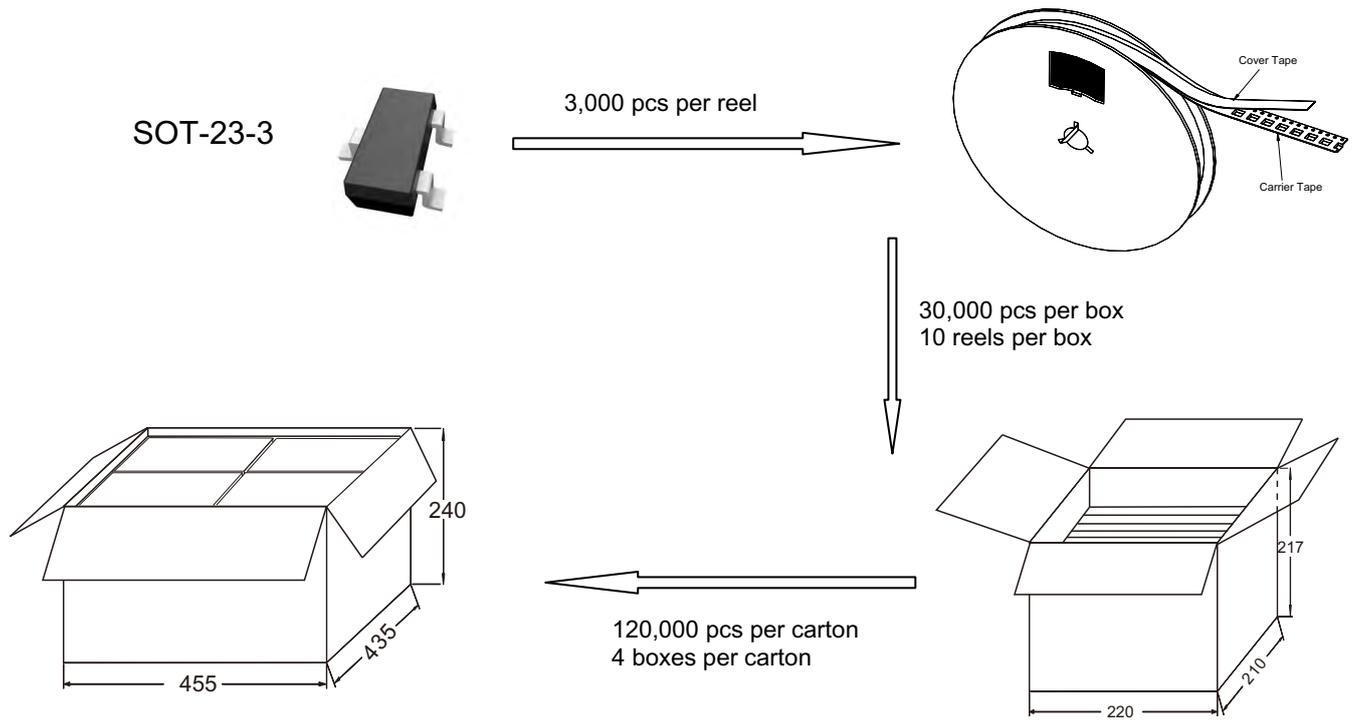
- Temperature: 370 °C
- Time: 3s max.
- Times: one time

### ◆ Storage conditions

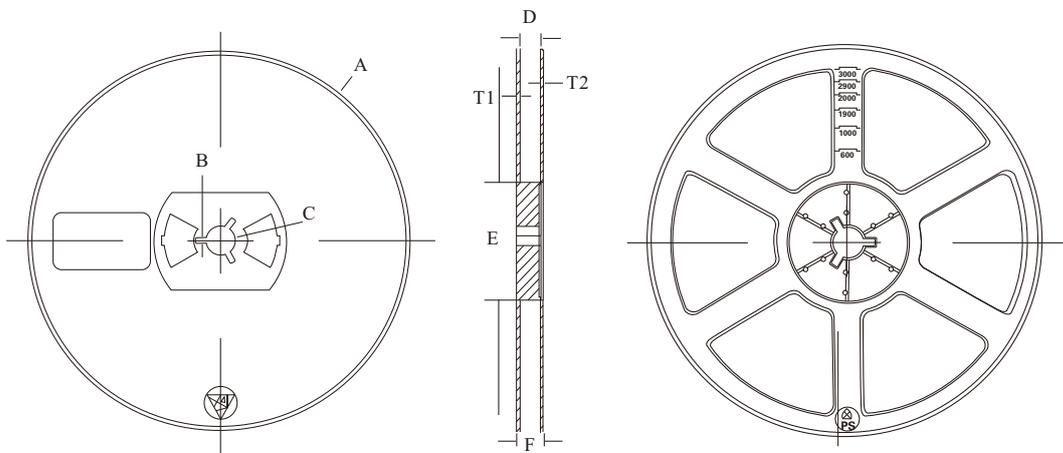
- **Temperature**  
5 to 40 °C
- **Humidity**  
30 to 80% RH
- **Recommended period**  
One year after manufacturing



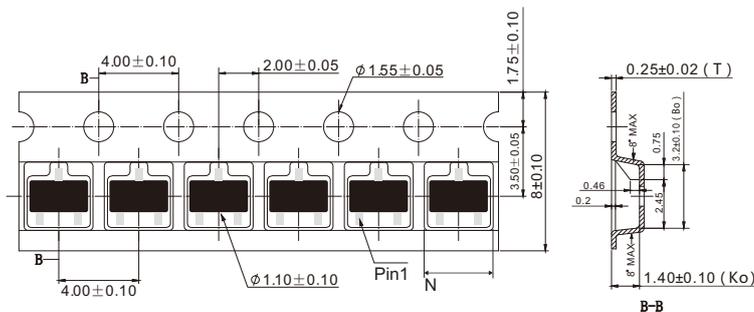
**Package Specifications**



**2. Tape and reel data(7inch Units:mm)**



Reel (7")



Tape (8mm)

Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2
N	3.15±0.1
G	1.22±0.1

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